TV30

Rectifier Diode

Replaces January 2000 version, DS4086-4.0

DS4086-5.0 February 2004

APPLICATIONS

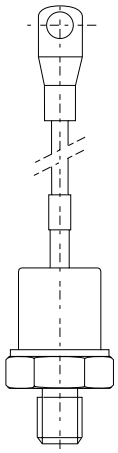
- Rectification
- Freewheel Diode
- DC Motor Control
- Power Supplies
- Welding
- Battery Chargers

KEY PARAMETERS

V_{RRM}	2000V
$I_{F(AV)}$	335A
I_{FSM}	6000A

FEATURES

- High Surge Capability



Outline type code: DO9
See Package Details for further information.

Fig. 1 Package outline

VOLTAGE RATINGS

Type Number	Repetitive Peak Reverse Voltage V_{RRM} V	Conditions
TV30 20 M or K(R) TV30 14 M or K(R) TV30 10 M or K(R) TV30 06 M or K(R)	2000 1400 1000 600	$V_{RSM} = V_{RRM} + 100V$

Lower voltage grades available.
M for M16 thread. K for 3/4" - 16UNF thread, R for reverse polarity.

CURRENT RATINGS

Symbol	Parameter	Conditions	Max.	Units
Single Side Cooled				
$I_{F(AV)}$	Mean forward current	Half wave resistive load, T_{case} = 100°C	335	A
$I_{F(RMS)}$	RMS value	T_{case} = 100°C	525	A
I_F	Continuous (direct) forward current	T_{case} = 100°C	440	A

SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I_{FSM}	Surge (non-repetitive) forward current	10ms half sine; T_{case} = 175°C	4.8	kA
I^2t	I^2t for fusing	V_R = 50% V_{RRM} - 1/4 sine	115 x 10^6	A^2s
I_{FSM}	Surge (non-repetitive) forward current	10ms half sine; T_{case} =175°C	6.0	kA
I^2t	I^2t for fusing	V_R = 0	180 x 10^3	A^2s

THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions	Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - junction to case	dc	-	0.13	°C/W
$R_{th(c-h)}$	Thermal resistance - case to heatsink	Mounting torque 35.0Nm with mounting compound	-	0.06	°C/W
T_{vj}	Virtual junction temperature	Forward (conducting)	-	175	°C
		Reverse (blocking)	-	175	°C
T_{stg}	Storage temperature range		-55	200	°C
-	Mounting Torque		30.0	35.0	Nm

CHARACTERISTICS

Symbol	Parameter	Conditions	Typ.	Max.	Units
V_{FM}	Forward voltage	At 1000A peak, T_{case} = 25°C	-	1.4	V
I_{RRM}	Peak reverse current	At V_{RRM}, T_{case} = 175°C	-	20	mA
Q_S	Total stored charge	I_F = 200A, dI_{RR}/dt = 20A/µs, T_{case} = 25˚C	300*	-	µC
I_{RM}	Peak recovery current		90*	-	A
t_{rr}	reverse recovery time		6.5*	-	µs
V_{TO}	Threshold voltage	At T_{vj} = 175˚C	-	0.8	V
r_T	Slope resistance	At T_{vj} = 175˚C	-	0.6	mΩ

**Typical values.*

CURVES

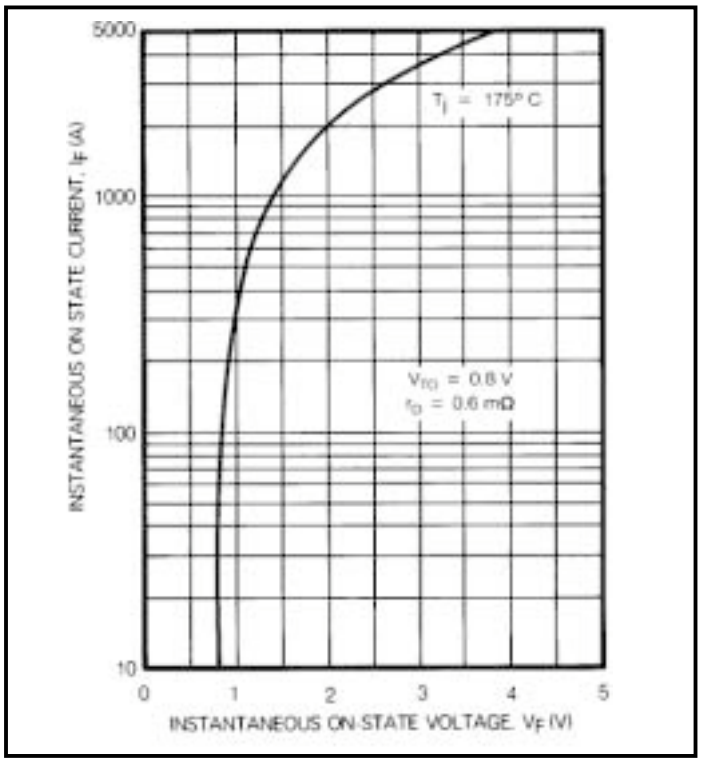


Fig.2 Maximum (limit) forward characteristics

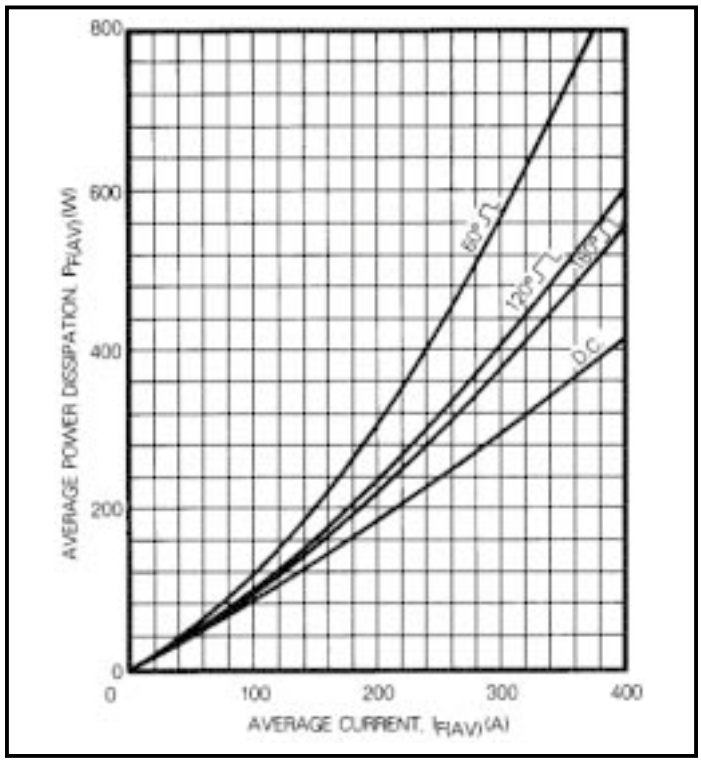


Fig.3 Power dissipation

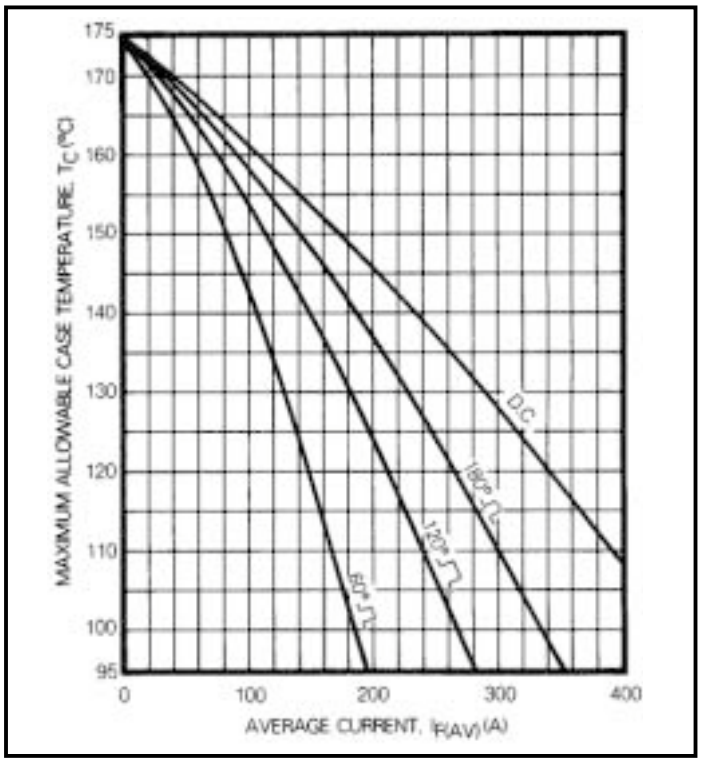


Fig.4 Maximum Tcase vs forward current

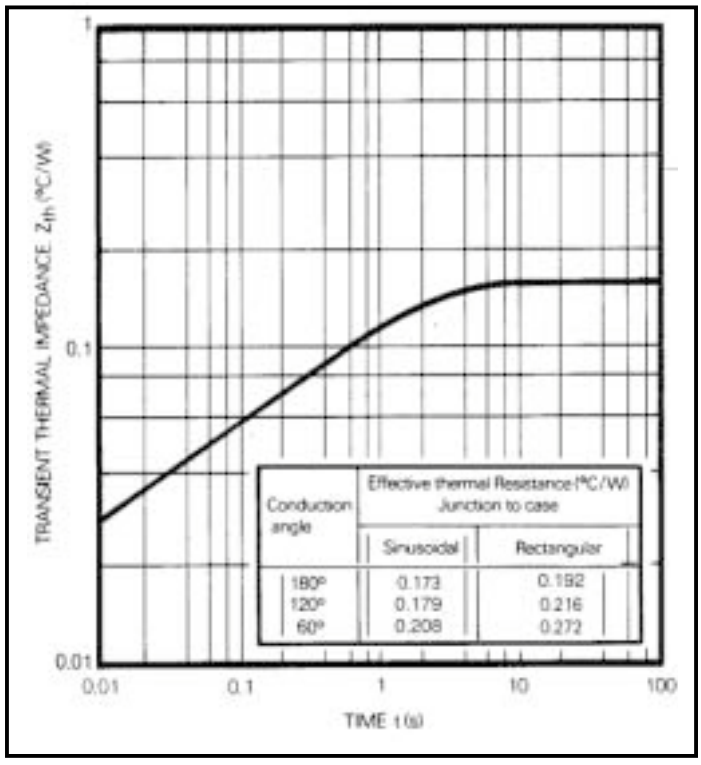


Fig.5 Tranient thermal impedance - Junction to case

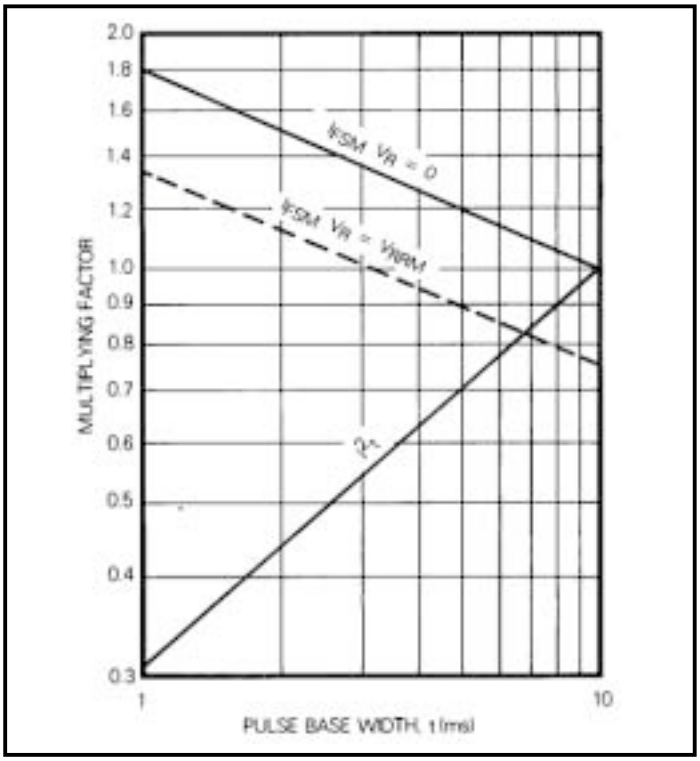


Fig.6 Non-rep. sub-cycle forward current and I^2t rating

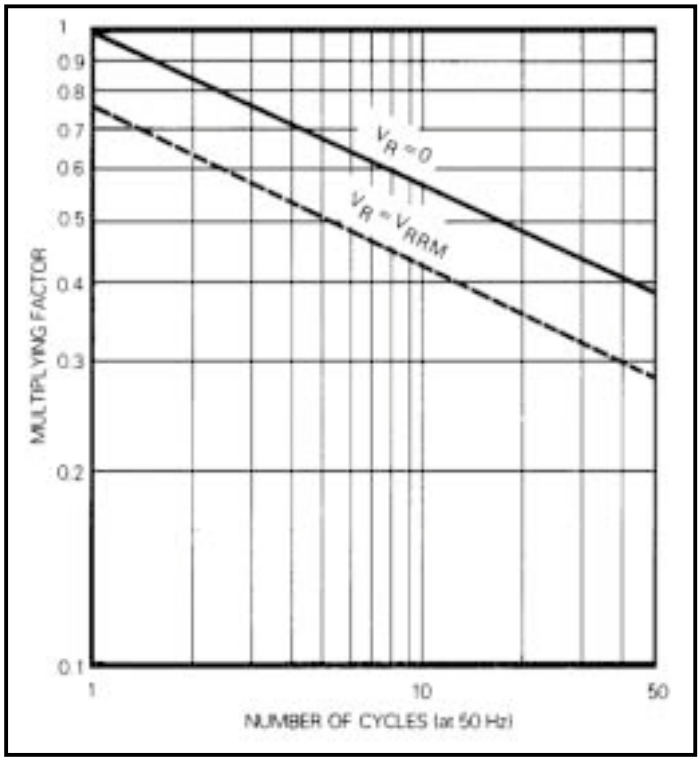
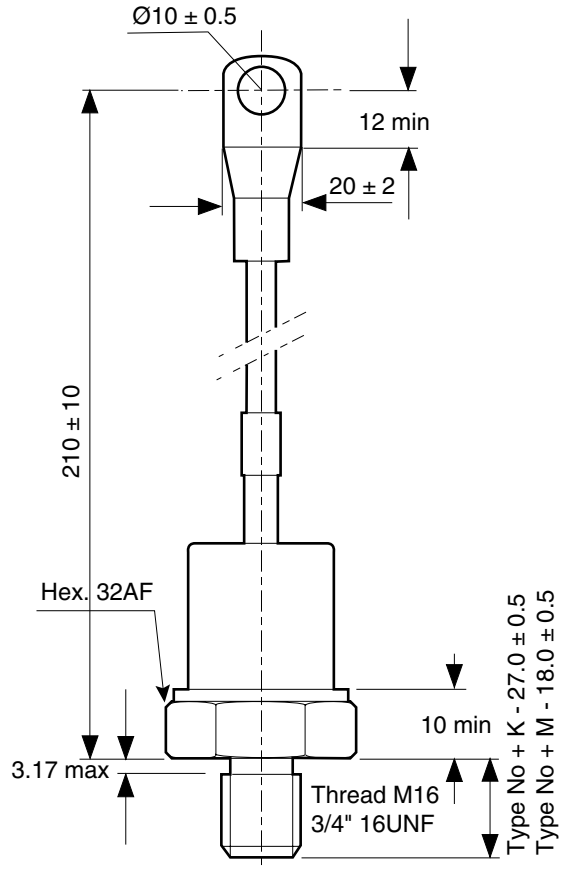


Fig.7 Multiplying factor for non-repetitive forward current

PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise.
DO NOT SCALE.



Package outline type code: DO9

Fig.8 Package details

POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group offers high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks which have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.

Stresses above those listed in this data sheet may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed.

http://www.dynexsemi.com

e-mail: power_solutions@dynexsemi.com

HEADQUARTERS OPERATIONS
DYNEX SEMICONDUCTOR LTD
Doddington Road, Lincoln.
Lincolnshire. LN6 3LF. United Kingdom.
Tel: +44-(0)1522-500500
Fax: +44-(0)1522-500550

CUSTOMER SERVICE
Tel: +44 (0)1522 502753 / 502901. Fax: +44 (0)1522 500020

SALES OFFICES
Benelux, Italy & Switzerland: Tel: +33 (0)1 60 69 32 36. Fax: +33 (0)1 60 69 31 97.
France: Tel: +33 (0)2 47 55 75 53. Fax: +33 (0)2 47 55 75 59. Tel: +33 (0)1 60 69 32 36. Fax: +33 (0)1 60 69 31 97
Germany, Northern Europe, Spain & Rest Of World: Tel: +44 (0)1522 502753 / 502901.
Fax: +44 (0)1522 500020
North America: Tel: (440) 259-2060. Fax: (440) 259-2059. Tel: (949) 733-3005. Fax: (949) 733-2986.

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